

# DATA SHEET

## **TEA1114A**

Low voltage telephone  
transmission circuit with dialler  
interface and regulated strong  
supply

Product specification  
Supersedes data of 1999 Sep 14  
File under Integrated Circuits, IC03

2000 Mar 21

# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

## TEA1114A

### FEATURES

- Low DC line voltage; operates down to 1.45 V (excluding voltage drop over external polarity guard)
- Line voltage regulator with adjustable DC voltage
- 3.3 V regulated strong supply point for peripheral circuits compatible with:
  - Speech mode
  - Ringer mode
  - Trickle mode.
- Transmit stage with:
  - Microphone amplifier with symmetrical high impedance inputs
  - DTMF amplifier with confidence tone on receive output.
- Receive stage with:
  - Receive amplifier with asymmetrical output
  - Earpiece amplifier with adjustable gain (and gain boost facility) for all types of earpieces.
- $\overline{\text{MUTE}}$  input for pulse or DTMF dialling
- AGC line loss compensation for microphone and receive amplifiers.

### APPLICATIONS

- Line powered telephone sets with LCD module
- Cordless telephones
- Fax machines
- Answering machines.

### GENERAL DESCRIPTION

The TEA1114A is a bipolar integrated circuit that performs all speech and line interface functions required in fully electronic telephone sets. It performs electronic switching between speech and dialling. The IC operates at a line voltage down to 1.45 V DC (with reduced performance) to facilitate the use of telephone sets connected in parallel.

When the line current is high enough, a fixed amount of current is derived from the LN pin in order to create a strong supply point at pin  $V_{DD}$ . The voltage at pin  $V_{DD}$  is regulated to 3.3 V to supply peripherals such as dialler, LCD module and microcontroller.

### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
TEA1114A	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
TEA1114AT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
TEA1114AUH	–	bare die; on foil	–

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### QUICK REFERENCE DATA

$I_{line} = 15 \text{ mA}$ ;  $V_{EE} = 0 \text{ V}$ ;  $R_{SLPE} = 20 \text{ }\Omega$ ; AGC pin connected to  $V_{EE}$ ;  $Z_{line} = 600 \text{ }\Omega$ ;  $f = 1 \text{ kHz}$ ; measured according to test circuits given in Figs 15, 16 and 17;  $T_{amb} = 25 \text{ }^\circ\text{C}$  for TEA1114A(T);  $T_j = 25 \text{ }^\circ\text{C}$  for TEA1114AUH; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{line}$	line current operating range	normal operation	11	–	140	mA
		with reduced performance	1	–	11	mA
$V_{LN}$	DC line voltage		4.05	4.35	4.65	V
$I_{CC}$	internal current consumption	$V_{CC} = 3.6 \text{ V}$	–	1.25	1.5	mA
$V_{CC}$	supply voltage for internal circuitry (unregulated)	$I_P = 0 \text{ mA}$	–	3.6	–	V
$V_{DD}$	regulated supply voltage for peripherals speech mode ringer mode	$I_{DD} = -3 \text{ mA}$	3.0	3.3	3.6	V
		$I_{DD} = 75 \text{ mA}$	3.0	3.3	3.6	V
$I_{DD}$	available supply current for peripherals		–	–	–3	mA
$G_{V(TX)}$	typical voltage gain for microphone amplifier	$V_{MIC} = 4 \text{ mV (RMS)}$	43.2	44.2	45.2	dB
$G_{V(RX)}$	typical voltage gain for receiving amplifier	$V_{IR} = 4 \text{ mV (RMS)}$	32.4	33.4	34.4	dB
$\Delta G_{V(QR)}$	gain setting range for earpiece amplifier	$R_{E1} = 100 \text{ k}\Omega$	–14	–	+12	dB
$\Delta G_{V(trx)}$	gain control range for microphone and receive amplifiers with respect to $I_{line} = 15 \text{ mA}$	$I_{line} = 85 \text{ mA}$	–	6.0	–	dB
$\Delta G_{V(trx)(m)}$	gain reduction for microphone and receive amplifiers	$\overline{MUTE} = \text{LOW}$	–	80	–	dB

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BLOCK DIAGRAM

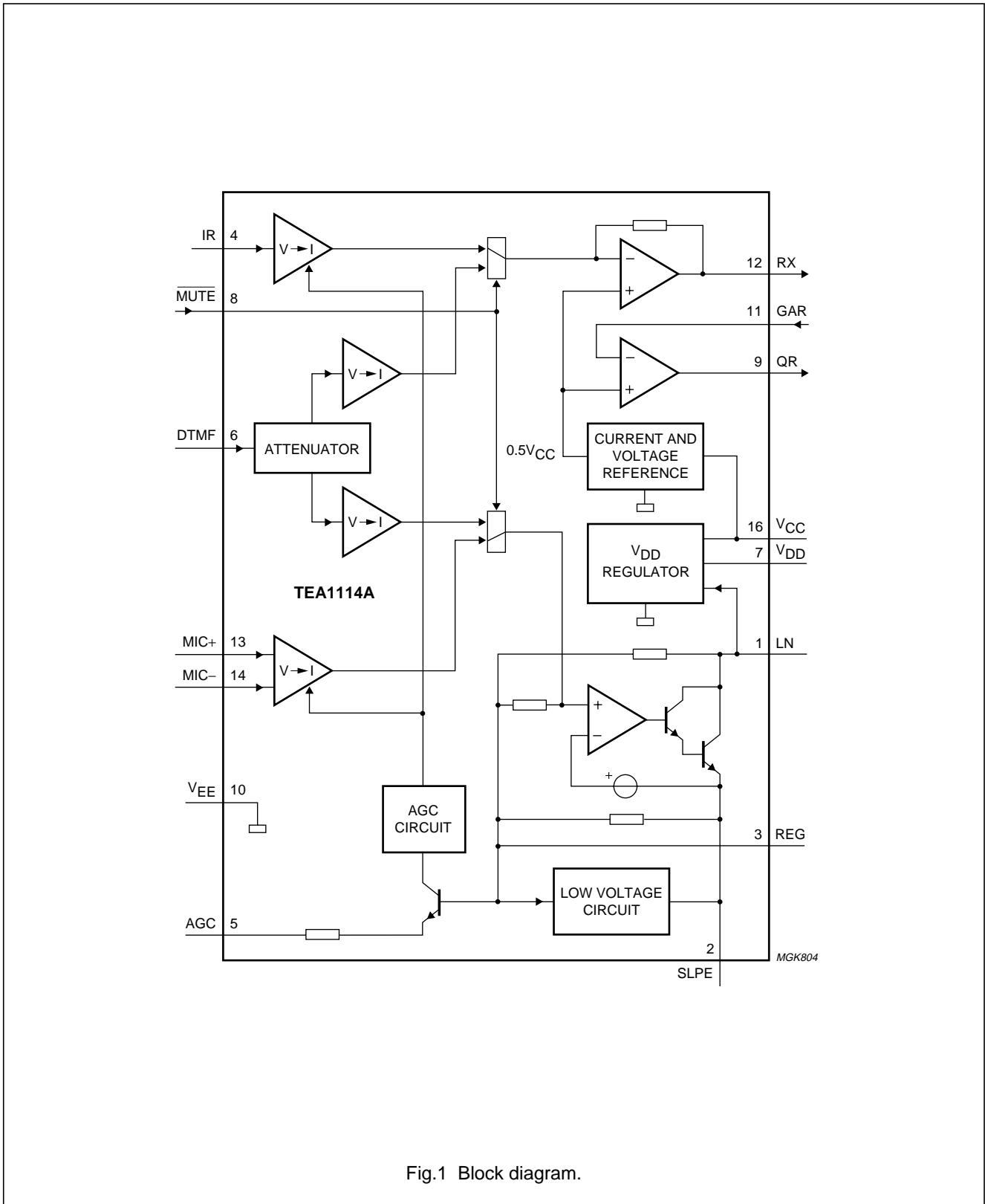


Fig.1 Block diagram.

Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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PINNING

SYMBOL	PIN	PAD	DESCRIPTION
	TEA1114A(T)	TEA1114AUH	
LN	1	1, 19	positive line terminal
SLPE	2	2	slope (DC resistance) adjustment
REG	3	3	line voltage regulator decoupling
IR	4	4	receiving amplifier input
AGC	5	5	automatic gain control/ line loss compensation
DTMF	6	6	dual-tone multi-frequency input
V <sub>DD</sub>	7	7	regulated supply for peripherals
$\overline{\text{MUTE}}$	8	8	mute input to select speech or dialling mode (active LOW)
QR	9	9	earpiece amplifier output
n.c.	–	10	not connected
V <sub>EE</sub>	10	11	negative line terminal
n.c.	–	12	not connected
GAR	11	13	earpiece amplifier gain adjustment
RX	12	14	receive amplifier output
MIC+	13	15	non-inverting microphone amplifier input
MIC–	14	16	inverting microphone amplifier input
n.c.	15	–	not connected
V <sub>CC</sub>	16	17	supply voltage for internal circuit
n.c.	–	18	not connected

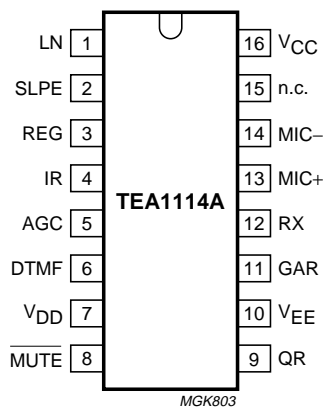


Fig.2 Pin configuration.

# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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### FUNCTIONAL DESCRIPTION

All data given in this chapter are typical values, except when otherwise specified.

#### Supply (pins LN, SLPE, REG, V<sub>CC</sub> and V<sub>DD</sub>)

The supply for the TEA1114A and its peripherals is obtained from the telephone line (see Fig.3).

#### THE LINE INTERFACE (PINS LN, SLPE AND REG)

The IC generates a stabilized reference voltage ( $V_{ref}$ ) between pins LN and SLPE.  $V_{ref}$  is temperature compensated and can be adjusted by means of an external resistor ( $R_{VA}$ ).  $V_{ref}$  equals 4.15 V and can be increased by connecting  $R_{VA}$  between pins REG and SLPE or decreased by connecting  $R_{VA}$  between pins REG and LN. The voltage at pin REG is used by the internal regulator to generate  $V_{ref}$  and is decoupled by  $C_{REG}$ , which is connected to  $V_{EE}$ . This capacitor, converted into an equivalent inductance (see Section "Set impedance") realizes the set impedance conversion from its DC value ( $R_{SLPE}$ ) to its AC value ( $R_{CC}$  in the audio-frequency range). The voltage at pin SLPE is proportional to the line current.

The voltage at pin LN is:

$$V_{LN} = V_{ref} + R_{SLPE} \times I_{SLPE}$$

$$I_{SLPE} = I_{line} - I_{CC} - I_P - I_{SUP}$$

where:

$I_{line}$  = line current

$I_{CC}$  = current consumption of the IC

$I_P$  = supply current for external circuits

$I_{SUP}$  = current consumed between LN and  $V_{EE}$  by the  $V_{DD}$  regulator.

The preferred value for  $R_{SLPE}$  is 20  $\Omega$ . Changing  $R_{SLPE}$  will affect more than the DC characteristics; it also influences the microphone and DTMF gains, the gain control characteristics, the sidetone level and the maximum output swing on the line.

The DC line current flowing into the set is determined by the exchange supply voltage ( $V_{EXCH}$ ), the feeding bridge resistance ( $R_{EXCH}$ ), the DC resistance of the telephone line ( $R_{line}$ ) and the reference voltage ( $V_{ref}$ ). With line currents below 9 mA, the internal reference voltage (generating  $V_{ref}$ ) is automatically adjusted to a lower value. This means that more sets can operate in parallel with DC line voltages (excluding the polarity guard) down to an absolute minimum voltage of 1.45 V. At currents below 9 mA, the circuit has limited sending and receiving levels. This is called the low voltage area.

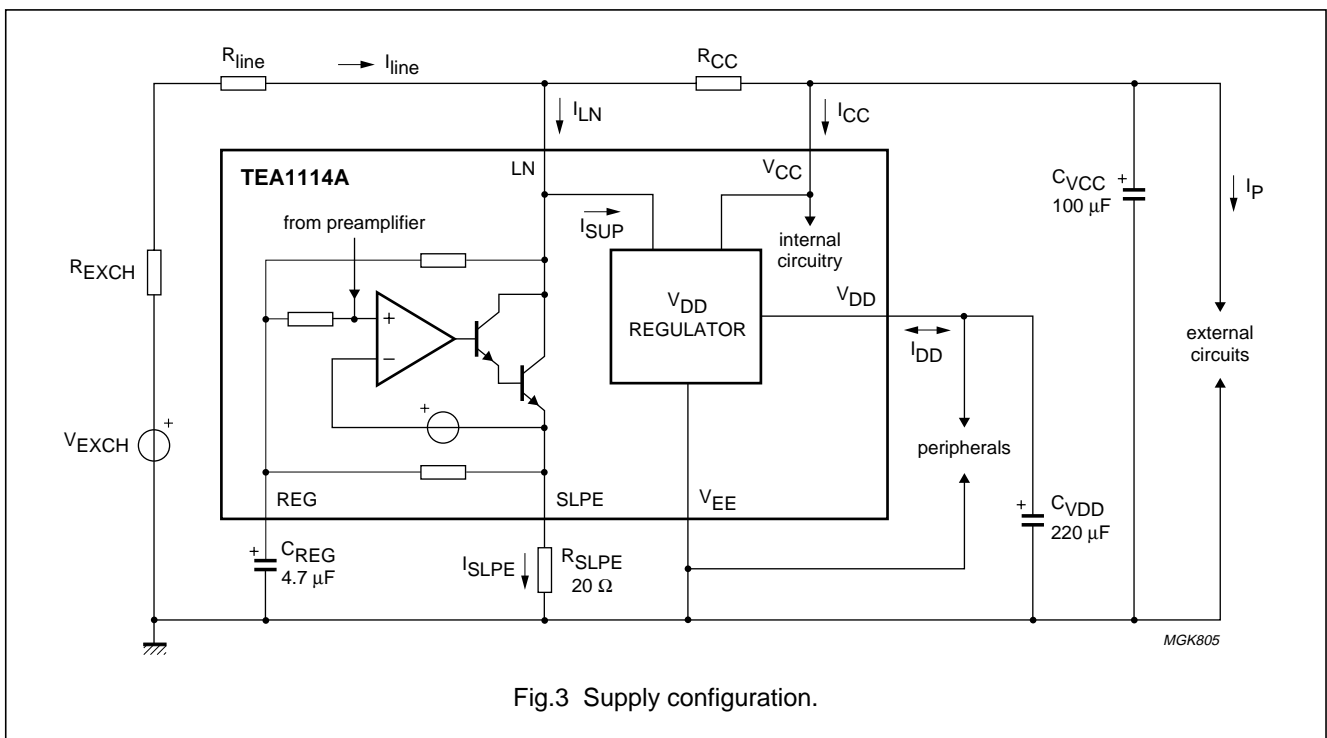


Fig.3 Supply configuration.

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### THE INTERNAL SUPPLY POINT (PIN $V_{CC}$ )

The internal circuitry of the TEA1114A is supplied from pin  $V_{CC}$ . This voltage supply is derived from the line voltage by means of a resistor ( $R_{CC}$ ) and must be decoupled by a capacitor  $C_{V_{CC}}$ . It may also be used to supply some external circuits. The  $V_{CC}$  voltage depends on the current consumed by the IC and the peripheral circuits as:  $V_{CC0} = V_{LN} - R_{CC} \times I_{CC}$

$$V_{CC} = V_{CC0} - R_{CC} \times (I_P + I_{rec})$$

(see also Figs 4 and 5).  $I_{rec}$  is the current consumed by the output stage of the earpiece amplifier.

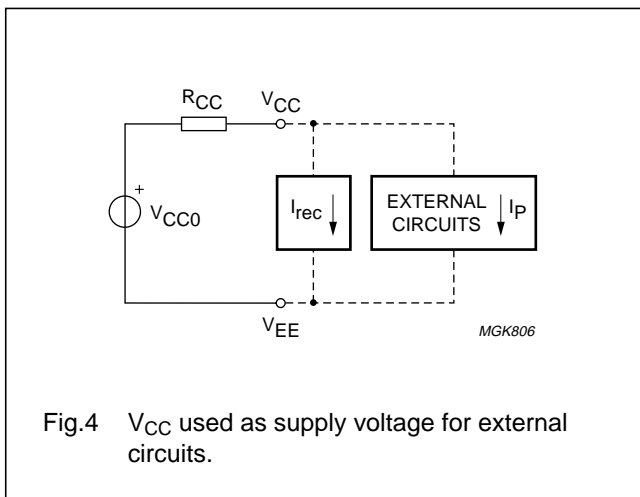


Fig.4  $V_{CC}$  used as supply voltage for external circuits.

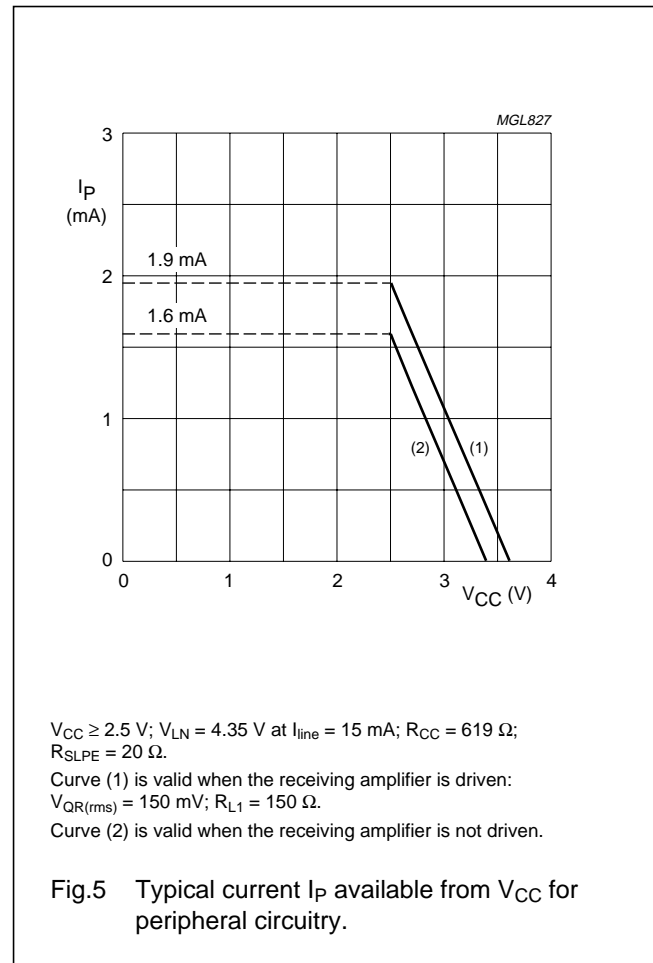


Fig.5 Typical current  $I_P$  available from  $V_{CC}$  for peripheral circuitry.

### THE REGULATED SUPPLY POINT (PIN $V_{DD}$ )

The  $V_{DD}$  regulator delivers a stabilized voltage for the peripherals in transmission mode (nominal  $V_{LN}$ ) as well as in ringer mode ( $V_{LN} = 0 \text{ V}$ ). The regulator (see Fig.6) consists of a sense input circuit, a current switch and a  $V_{DD}$  output stabilizer. The regulator operates as a current source at the LN input in transmission mode; it takes a constant current of 4.3 mA (at nominal conditions) from pin LN. The current switch reduces the distortion on the line at large signal swings. Output  $V_{DD}$  follows the DC voltage at pin LN (with typically 0.35 V difference) up to  $V_{DD} = 3.3 \text{ V}$ . The input current of the regulator is constant while the output (source) current is determined by the consumption of the peripherals. The difference between input and output current is shunted by the internal  $V_{DD}$  stabilizer.

In ringer mode, the stabilizer operates as a shunt stabilizer to keep  $V_{DD}$  at 3.3 V. In this mode, the input voltage  $V_{LN} = 0 \text{ V}$  while the input current into pin  $V_{DD}$  is delivered by the ringing signal.  $V_{DD}$  has to be decoupled by a capacitor  $C_{V_{DD}}$ .

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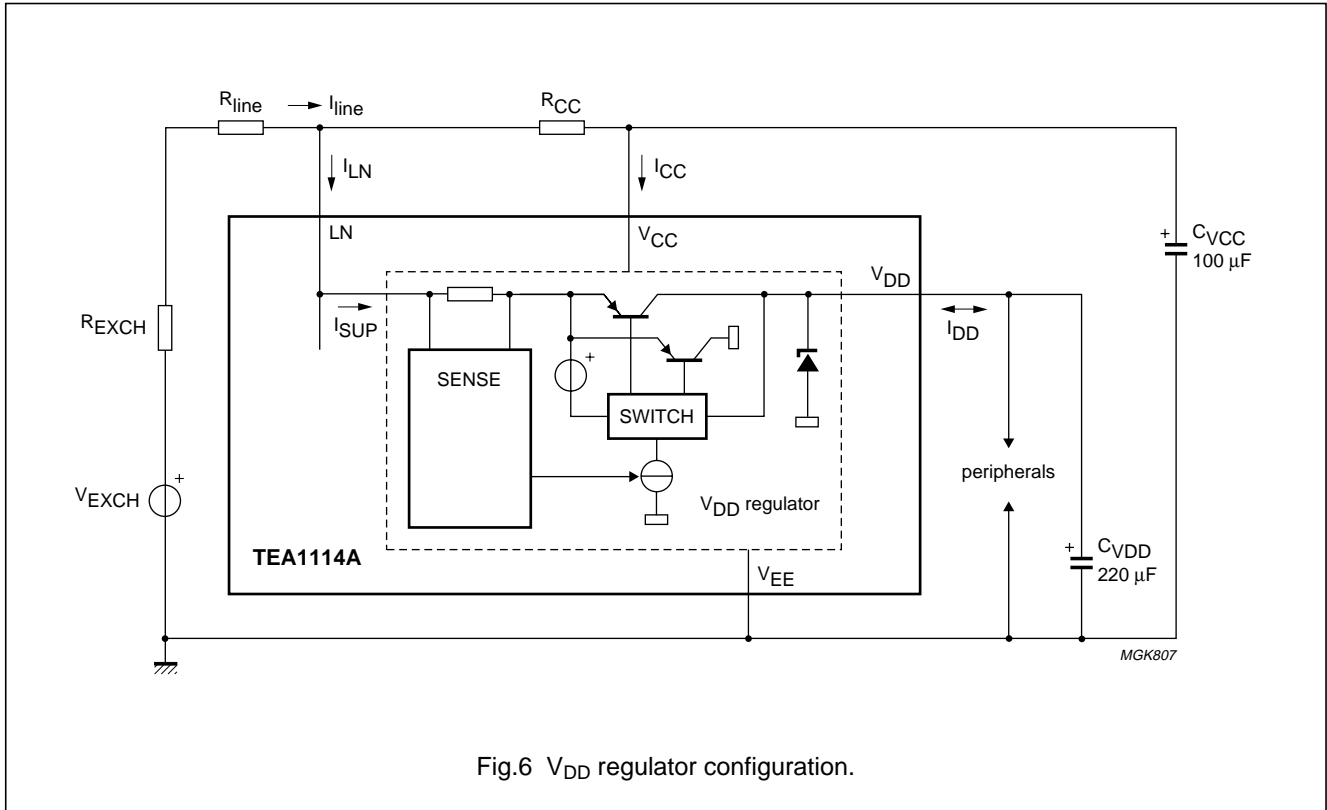
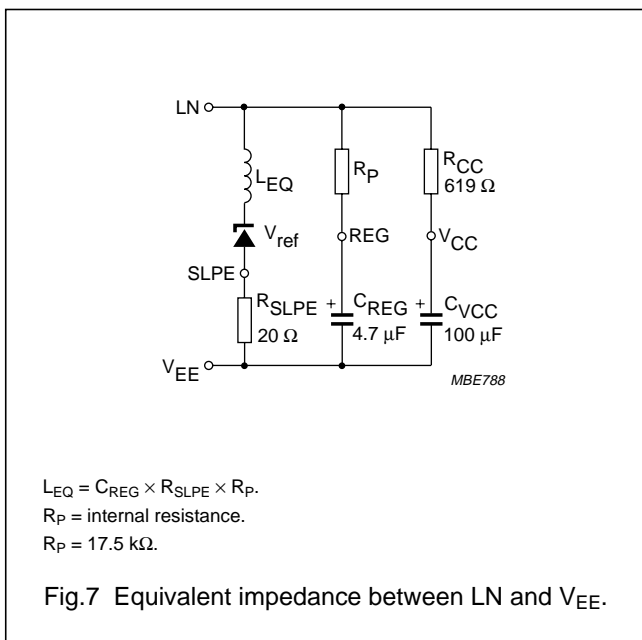


Fig.6 VDD regulator configuration.

Set impedance

In the audio frequency range, the dynamic impedance is mainly determined by the RCC resistor. The equivalent impedance of the circuit is illustrated in Fig.7.



Transmit stage (pins MIC+, MIC- and DTMF)

MICROPHONE AMPLIFIER (PINS MIC+ AND MIC-)

The TEA1114A has symmetrical microphone inputs. The input impedance between pins MIC+ and MIC- is 64 kΩ (2 × 32 kΩ). The voltage gain from pins MIC+/MIC- to pin LN is set at 44.2 dB (typically).

Automatic gain control is provided on this amplifier for line loss compensation.

DTMF AMPLIFIER (PIN DTMF)

When the DTMF amplifier is enabled, dialling tones may be sent on line. These tones are also sent to the receive output RX at a low level (confidence tone).

The TEA1114A has an asymmetrical DTMF input. The input impedance between DTMF and VEE is 20 kΩ. The voltage gain from pin DTMF to pin LN is set at 26 dB.

Automatic gain control has no effect on the DTMF amplifier.



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### Receiving stage (pins IR, RX, GAR and QR)

The receive part consists of a receive amplifier and an earpiece amplifier.

#### THE RECEIVE AMPLIFIER (PINS IR AND RX)

The receive amplifier transfers the receive signal from input IR to output RX. The input impedance of the receive amplifier, between pins IR and  $V_{EE}$ , is 20 kΩ. The voltage gain from pin IR to RX is set at 33.4 dB. RX output is intended to drive high ohmic (real) loads. Automatic gain control is provided on the receive amplifier.

#### THE EARPIECE AMPLIFIER (PINS GAR AND QR)

The earpiece amplifier is an operational amplifier having its output (QR) and inverting input (GAR) available. It can be used in conjunction with two resistors to get some extra gain or attenuation.

In an usual configuration (see Fig.8), output RX drives the earpiece amplifier by means of  $R_{E1}$  connected between RX and GAR. Feedback resistor  $R_{E2}$  of the earpiece amplifier is connected between QR and GAR. Output QR drives the earpiece.

The gain of the earpiece amplifier (from RX to QR) can be set between +12 and -14 dB by means of resistor  $R_{E2}$ .

The preferred value of  $R_{E1}$  is 100 kΩ.

The earpiece amplifier offers a gain boost facility relative to the initial gain. Resistor  $R_{E2}$  has to be replaced by the network of  $R_{E21}$ ,  $R_{E22}$  and  $R_{E23}$  as shown in Fig.8.

The initial gain is defined by: 
$$-\frac{R_{E21} + R_{E22}}{R_{E1}}$$

which corresponds to  $R_{E23} = \infty$ . The gain boost is realized by a defined value of  $R_{E23}$  and is:

$$-\frac{R_{E21} + R_{E22}}{R_{E1}} \times \left(1 + \frac{R_{E21} // R_{E22}}{R_{E23}}\right)$$

Two external capacitors  $C_{GAR}$  (connected between GAR and QR) and  $C_{GARS}$  (connected between GAR and  $V_{EE}$ ) ensure stability. The  $C_{GAR}$  capacitor provides a first-order low-pass filter. The cut-off frequency corresponds to the time constant  $C_{GAR} \times R_{E2}$ . The relationship  $C_{GARS} = 10 \times C_{GAR}$  must be fulfilled to ensure stability.

The output voltages of both amplifiers are specified for continuous wave drive. The maximum output swing depends on the DC line voltage  $V_{LN}$ , the  $R_{CC}$  resistor, the  $I_{CC}$  current consumption of the circuit, the  $I_P$  current consumption of the peripheral circuits and the load impedance.

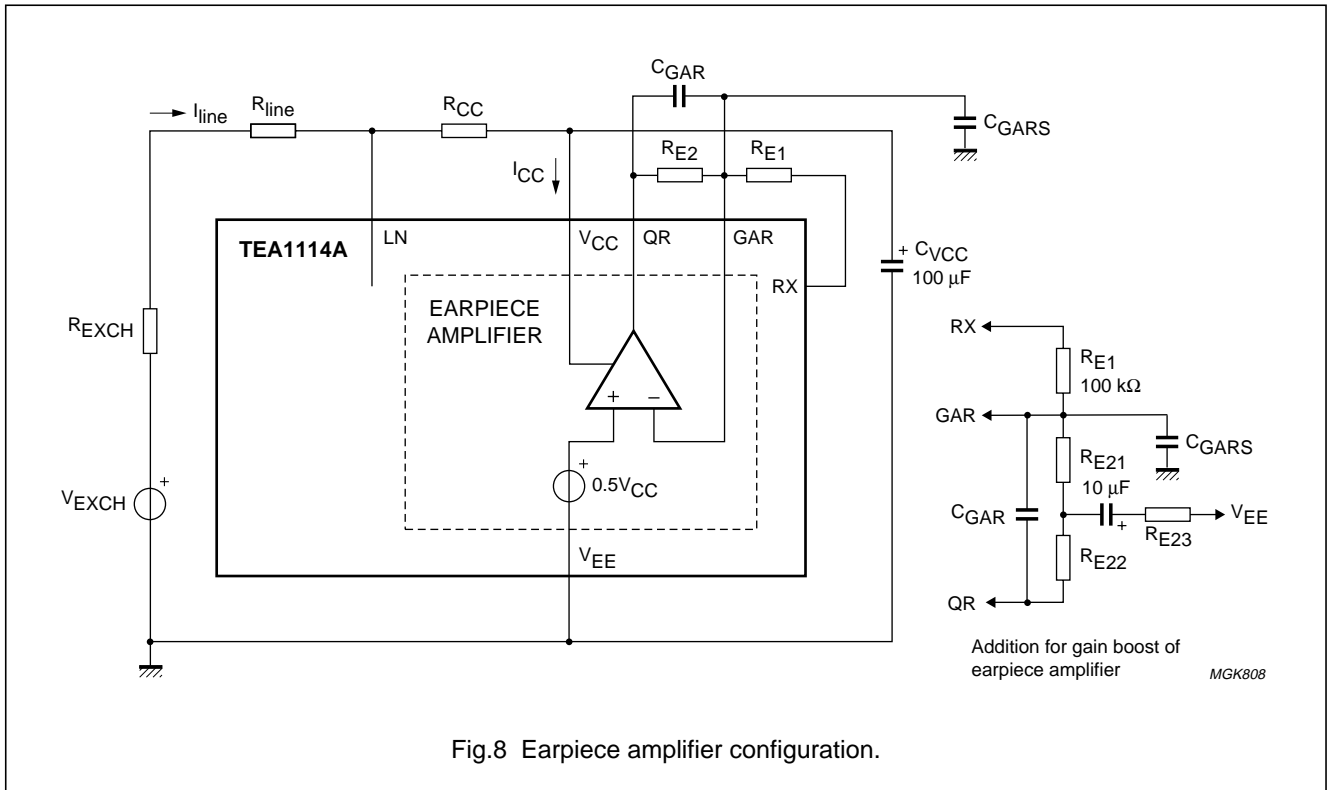


Fig.8 Earpiece amplifier configuration.

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### Automatic gain control (pin AGC)

The TEA1114A performs automatic line loss compensation. The automatic gain control varies the gain of the microphone amplifier and the gain of the receive amplifier in accordance with the DC line current.

The control range is 6.0 dB (which corresponds approximately to a line length of 5 km for a 0.5 mm diameter twisted-pair copper cable with a DC resistance of 176  $\Omega$ /km and an average attenuation of 1.2 dB/km).

The IC can be used with different configurations of feeding bridge (supply voltage and bridge resistance) by connecting an external resistor  $R_{AGC}$  between pins AGC and  $V_{EE}$ . This resistor enables the  $I_{start}$  and  $I_{stop}$  line currents to be increased (the ratio between  $I_{start}$  and  $I_{stop}$  is not affected by the resistor). The AGC function is disabled when pin AGC is left open-circuit.

### Mute function (pin $\overline{MUTE}$ )

The mute function performs the switching between the speech mode and the dialling mode.

When  $\overline{MUTE}$  is LOW, the DTMF input is enabled and the microphone and receive amplifier inputs are disabled. In this mode, the DTMF tones are sent to the receive output at a low level (confidence tone).

When  $\overline{MUTE}$  is HIGH, the microphone and receiving amplifiers inputs are enabled while the DTMF input is disabled. The  $\overline{MUTE}$  input is provided with an internal pull-up current source to  $V_{CC}$ .

### Sidetone suppression

The TEA1114A anti-sidetone network comprising  $R_{CC} // Z_{line}$ ,  $R_{ast1}$ ,  $R_{ast2}$ ,  $R_{ast3}$ ,  $R_{SLPE}$  and  $Z_{bal}$  (see Fig.9) suppresses the transmitted signal in the earpiece. Maximum compensation is obtained when the following conditions are fulfilled:

$$R_{SLPE} \times R_{ast1} = R_{CC} \times (R_{ast2} + R_{ast3})$$

$$k = \frac{R_{ast2} \times (R_{ast3} + R_{SLPE})}{R_{ast1} \times R_{SLPE}}$$

$$Z_{bal} = k \times Z_{line}$$

The scale factor  $k$  is chosen to meet the compatibility with a standard capacitor from the E6 or E12 range for  $Z_{bal}$ .

In practice,  $Z_{line}$  varies considerably with the line type and the line length. Therefore, the value of  $Z_{bal}$  should be for an average line length which gives satisfactory sidetone suppression with short and long lines. The suppression also depends on the accuracy of the match between  $Z_{bal}$  and the impedance of the average line.

The anti-sidetone network for the TEA1114A attenuates the receiving signal from the line by 32 dB before it enters the receiving amplifier. The attenuation is almost constant over the whole audio frequency range.

A Wheatstone bridge configuration (see Fig.10) may also be used.

More information on the balancing of an anti-sidetone bridge can be obtained in our publication "*Semiconductors for Wired Telecom Systems; Application Handbook, IC03b*". For ordering information please contact the Philips Semiconductors sales office.

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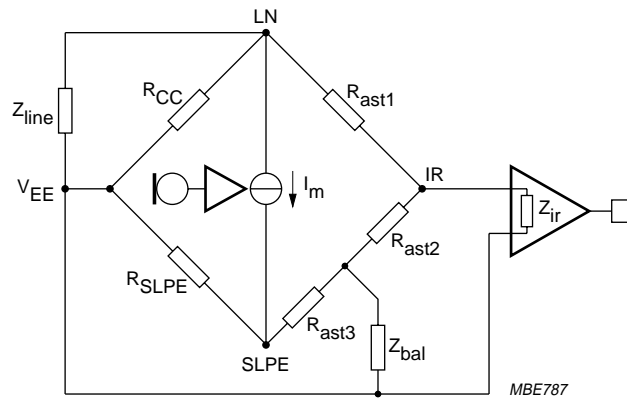


Fig.9 Equivalent circuit of TEA1114A anti-sidetone bridge.

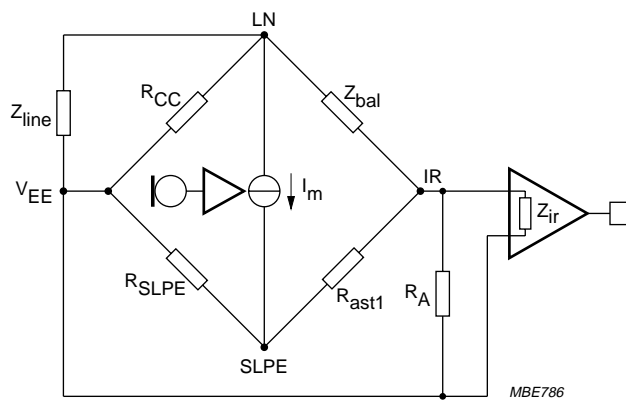


Fig.10 Equivalent circuit of an anti-sidetone network in a Wheatstone bridge configuration.

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## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>LN</sub>	positive continuous line voltage		V <sub>EE</sub> - 0.4	12	V
	repetitive line voltage during switch-on or line interruption		V <sub>EE</sub> - 0.4	13.2	V
I <sub>DD</sub>	maximum input current at pin V <sub>DD</sub>		-	75	mA
V <sub>n(max)</sub>	maximum voltage on all pins except pin V <sub>DD</sub>		V <sub>EE</sub> - 0.4	V <sub>CC</sub> + 0.4	V
I <sub>line</sub>	line current	R <sub>SLPE</sub> = 20 Ω; see Figs 11 and 12	-	140	mA
P <sub>tot</sub>	total power dissipation TEA1114A	T <sub>amb</sub> = 75 °C; see Figs 11 and 12	-	625	mW
	TEA1114AT		-	416	mW
	TEA1114AUH; note 1		-	-	
T <sub>stg</sub>	storage temperature		-40	+125	°C
T <sub>amb</sub>	ambient temperature		-25	+75	°C
T <sub>j</sub>	junction temperature		-	125	°C

### Note

- Mostly dependent on the maximum required ambient temperature, on the voltage between LN and SLPE and on the thermal resistance between die ambient temperature. This thermal resistance depends on the application board layout and on the materials used. Figure 13 shows the safe operating area versus this thermal resistance for ambient temperature T<sub>amb</sub> = 75 °C.

## THERMAL CHARACTERISTICS

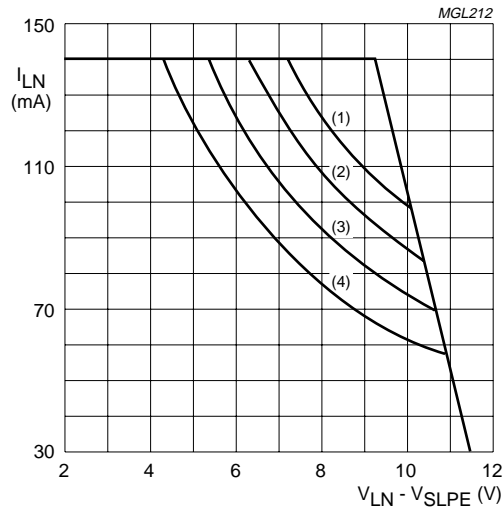
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air; note 1		
	TEA1114A		70	K/W
	TEA1114AT		115	K/W
	TEA1114AUH		tbf by customer application	K/W

### Note

- Mounted on epoxy board 40.1 × 19.1 × 1.5 mm.

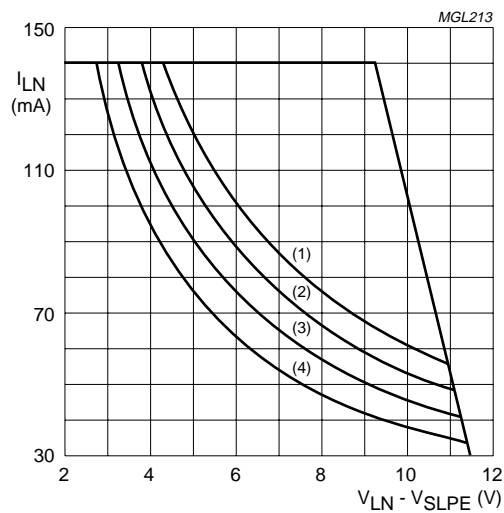
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- (1)  $T_{amb} = 45\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 1.000\text{ W}$ .
- (2)  $T_{amb} = 55\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 0.875\text{ W}$ .
- (3)  $T_{amb} = 65\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 0.750\text{ W}$ .
- (4)  $T_{amb} = 75\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 0.625\text{ W}$ .

Fig.11 DIP16 safe operating area (TEA1114A).

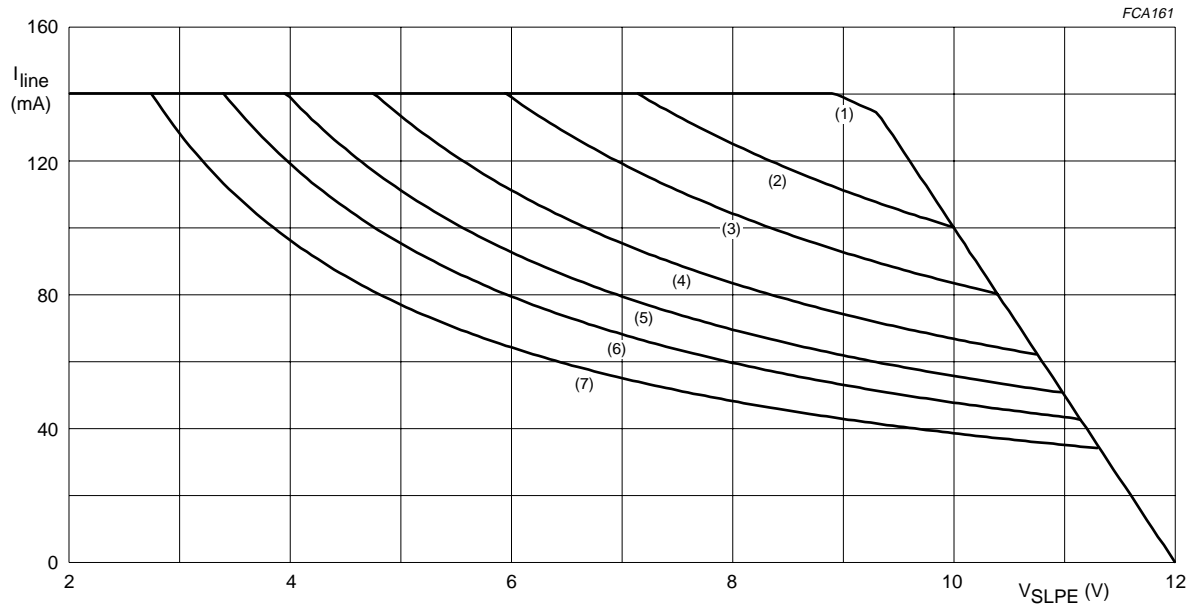


- (1)  $T_{amb} = 45\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 0.666\text{ W}$ .
- (2)  $T_{amb} = 55\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 0.583\text{ W}$ .
- (3)  $T_{amb} = 65\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 0.500\text{ W}$ .
- (4)  $T_{amb} = 75\text{ }^{\circ}\text{C}$ ;  $P_{tot} = 0.416\text{ W}$ .

Fig.12 SO16 safe operating area (TEA1114AT).

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LINE	R <sub>th(j-a)</sub> (K/W)
(1)	40
(2)	50
(3)	60
(4)	75
(5)	90
(6)	105
(7)	130

Fig.13 Safe operating area at T<sub>amb</sub> = 75 °C (TEA1114AUH).

# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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## CHARACTERISTICS

$I_{line} = 15 \text{ mA}$ ;  $V_{EE} = 0 \text{ V}$ ;  $R_{SLPE} = 20 \text{ }\Omega$ ; pin AGC connected to  $V_{EE}$ ;  $Z_{line} = 600 \text{ }\Omega$ ;  $f = 1 \text{ kHz}$ ; measured according to test circuits given in Figs 15, 16 and 17;  $T_{amb} = 25 \text{ }^\circ\text{C}$  for TEA1114A(T);  $T_j = 25 \text{ }^\circ\text{C}$  for TEA1114AUHT; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Supply (pins LN, V<sub>CC</sub>, SLPE, REG and V<sub>DD</sub>)</b>						
THE LINE INTERFACE (PINS LN, SLPE AND REG)						
$V_{ref}$	stabilized reference voltage between pins LN and SLPE		3.9	4.15	4.4	V
$V_{LN}$	DC line voltage	$I_{line} = 1 \text{ mA}$	–	1.45	–	V
		$I_{line} = 4 \text{ mA}$	–	2	–	V
		$I_{line} = 15 \text{ mA}$	4.05	4.35	4.65	V
		$I_{line} = 140 \text{ mA}$	–	7.1	7.55	V
$V_{LN(Ext)}$	DC line voltage with an external resistor $R_{VA}$	$R_{VA} = 44.2 \text{ k}\Omega$ (between pins LN and REG)	–	3.6	–	V
$\Delta V_{LN(T)}$	DC line voltage variation with temperature referred to 25 °C	$T_{amb} = -25 \text{ to } +75 \text{ }^\circ\text{C}$	–	$\pm 40$	–	mV
THE INTERNAL SUPPLY POINT (PIN V <sub>CC</sub> )						
$I_{CC}$	internal current consumption	$V_{CC} = 3.6 \text{ V}$	–	1.25	1.5	mA
$V_{CC}$	supply voltage for internal circuitry	$I_P = 0 \text{ mA}$	–	3.6	–	V
THE REGULATED SUPPLY POINT (PIN V <sub>DD</sub> )						
$I_{SUP}$	input current of the V <sub>DD</sub> regulator (current from pin LN not flowing through pin SLPE)	$I_{line} = 1 \text{ mA}$	–	0	–	mA
		$I_{line} = 4 \text{ mA}$	–	2.15	–	mA
		$I_{line} \geq 11 \text{ mA}$	–	4.3	–	mA
$V_{DD}$	regulated supply voltage in: speech mode	$I_{DD} = -3 \text{ mA}$ ; $V_{LN} > 3.6 + 0.25 \text{ V}$ (typ.); $I_{line} \geq 11 \text{ mA}$	3.0	3.3	3.6	V
	speech mode at reduced performance	$I_{line} = 4 \text{ mA}$	–	$V_{LN} - 0.35$	–	V
	ringer mode	$I_{line} = 0 \text{ mA}$ ; $I_{DD} = 75 \text{ mA}$	3.0	3.3	3.6	V
$I_{DD}$	regulated supply current available in: speech mode	$I_{line} \geq 11 \text{ mA}$	–	–	–3	mA
	speech mode at reduced performance	$I_{line} = 4 \text{ mA}$	–	–0.5	–	mA
	trickle mode	$I_{line} = 0 \text{ mA}$ ; $V_{CC}$ discharging; $V_{DD} = 1.2 \text{ V}$	–	–	100	nA

# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Transmit stage (pins MIC+, MIC– and DTMF)</b>						
MICROPHONE AMPLIFIER (PINS MIC+ AND MIC–)						
$ Z_i $	input impedance		–	68	–	k $\Omega$
	differential between pins MIC+ and MIC– single-ended between pins MIC+/MIC– and $V_{EE}$		–	34	–	k $\Omega$
$G_{V(TX)}$	voltage gain from pins MIC+/MIC– to pin LN	$V_{MIC} = 4 \text{ mV (RMS)}$	43.2	44.2	45.2	dB
$\Delta G_{V(TX)(f)}$	voltage gain variation with frequency referred to 1 kHz	$f = 300 \text{ to } 3400 \text{ Hz}$	–	$\pm 0.2$	–	dB
$\Delta G_{V(TX)(T)}$	voltage gain variation with temperature referred to 25 °C	$T_{amb} = -25 \text{ to } +75 \text{ }^\circ\text{C}$	–	$\pm 0.3$	–	dB
CMRR	common mode rejection ratio		–	80	–	dB
$V_{LN(max)(rms)}$	maximum sending signal (RMS value)	$I_{line} = 15 \text{ mA}; \text{THD} = 2\%$	1.8	2.15	–	V
		$I_{line} = 4 \text{ mA}; \text{THD} = 10\%$	–	0.35	–	V
$V_{no(LN)}$	noise output voltage at pin LN	psophometrically weighted (P53 curve); pins MIC+/MIC– shorted through 200 $\Omega$	–	–78	–	dBmp
DTMF AMPLIFIER (PIN DTMF)						
$ Z_i $	input impedance		–	21	–	k $\Omega$
$G_{V(DTMF)}$	voltage gain from pin DTMF to pin LN	$V_{DTMF} = 20 \text{ mV (RMS)};$ $MUTE = LOW$	25	26	27	dB
$\Delta G_{V(DTMF)(f)}$	voltage gain variation with frequency referred to 1 kHz	$f = 300 \text{ to } 3400 \text{ Hz}$	–	$\pm 0.2$	–	dB
$\Delta G_{V(DTMF)(T)}$	voltage gain variation with temperature referred to 25 °C	$T_{amb} = -25 \text{ to } +75 \text{ }^\circ\text{C}$	–	$\pm 0.4$	–	dB
$G_{V(ct)}$	voltage gain from pin DTMF to pin RX (confidence tone)	$V_{DTMF} = 20 \text{ mV (RMS)};$ $R_{L2} = 10 \text{ k}\Omega;$ $MUTE = LOW$	–	–9.2	–	dB
<b>Receiving stage (pins IR, RX, GAR and QR)</b>						
THE RECEIVE AMPLIFIER (PINS IR AND RX)						
$ Z_i $	input impedance		–	21.5	–	k $\Omega$
$G_{V(RX)}$	voltage gain from pin IR to pin RX	$V_{IR} = 4 \text{ mV (RMS)}$	32.4	33.4	34.4	dB
$\Delta G_{V(RX)(f)}$	voltage gain variation with frequency referred to 1 kHz	$f = 300 \text{ to } 3400 \text{ Hz}$	–	$\pm 0.2$	–	dB
$\Delta G_{V(RX)(T)}$	voltage gain variation with temperature referred to 25 °C	$T_{amb} = -25 \text{ to } +75 \text{ }^\circ\text{C}$	–	$\pm 0.3$	–	dB
$V_{RX(max)(rms)}$	maximum receiving signal on pin RX (RMS value)	$I_p = 0 \text{ mA};$ sine wave drive; $R_{L2} = 10 \text{ k}\Omega;$ $\text{THD} = 2\%$	0.4	–	–	V



# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$ I_{RX(max)} $	maximum source and sink current on pin RX (peak value)	$I_P = 0$ mA; sine wave drive	50	–	–	$\mu$ A
$V_{no(RX)(rms)}$	noise output voltage at pin RX (RMS value)	pin IR open-circuit; $R_{L2} = 10$ k $\Omega$ ; psophometrically weighted (P53 curve)	–	–86	–	dBVp
<b>THE EARPIECE AMPLIFIER (PINS GAR AND QR)</b>						
$G_{V(QR)}$	voltage gain from pin RX to pin QR	$V_{IR} = 4$ mV (RMS); $R_{E1} = R_{E2} = 100$ k $\Omega$	–	0	–	dB
$\Delta G_{V(QR)}$	voltage gain setting	$R_{E1} = 100$ k $\Omega$	–14	–	+12	dB
$V_{QR(max)(rms)}$	maximum receiving signal on pin QR (RMS value)	$I_P = 0$ mA; sine wave drive; $R_{L1} = 150$ $\Omega$ ; THD = 2%	0.3	0.38	–	V
		$I_P = 0$ mA; sine wave drive; $R_{L1} = 450$ $\Omega$ ; THD = 2%	0.46	0.56	–	V
$V_{no(QR)(rms)}$	noise output voltage at pin QR (RMS value)	IR open-circuit; $R_{L1} = 150$ $\Omega$ ; $R_{E1} = R_{E2} = 100$ k $\Omega$ psophometrically weighted (P53 curve)	–	–86	–	dBVp
		$R_{E1} = 100$ k $\Omega$ ; $R_{E2} = 25$ k $\Omega$	–	–98	–	dBVp
<b>Automatic gain control (pin AGC)</b>						
$\Delta G_{V(trx)}$	voltage gain control range for microphone and receive amplifiers with respect to $I_{line} = 15$ mA	$I_{line} = 85$ mA	–	6.0	–	dB
$I_{start}$	highest line current for maximum gain		–	23	–	mA
$I_{stop}$	lowest line current for minimum gain		–	59	–	mA
<b>Mute function (pin MUTE)</b>						
$V_{IL}$	LOW-level input voltage		$V_{EE} - 0.4$	–	$V_{EE} + 0.3$	V
$V_{IH}$	HIGH-level input voltage		$V_{EE} + 1.5$	–	$V_{CC} + 0.4$	V
$I_{MUTE}$	input current		–	2	10	$\mu$ A
$\Delta G_{V(trx)(m)}$	voltage gain reduction for:	microphone amplifier $\overline{MUTE} = LOW$	–	80	–	dB
		receive amplifier $\overline{MUTE} = LOW$	–	80	–	dB
		earpiece amplifier $\overline{MUTE} = LOW$	–	80	–	dB
		DTMF amplifier $\overline{MUTE} = HIGH$	–	80	–	dB

# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

## TEA1114A

### TEST AND APPLICATION INFORMATION

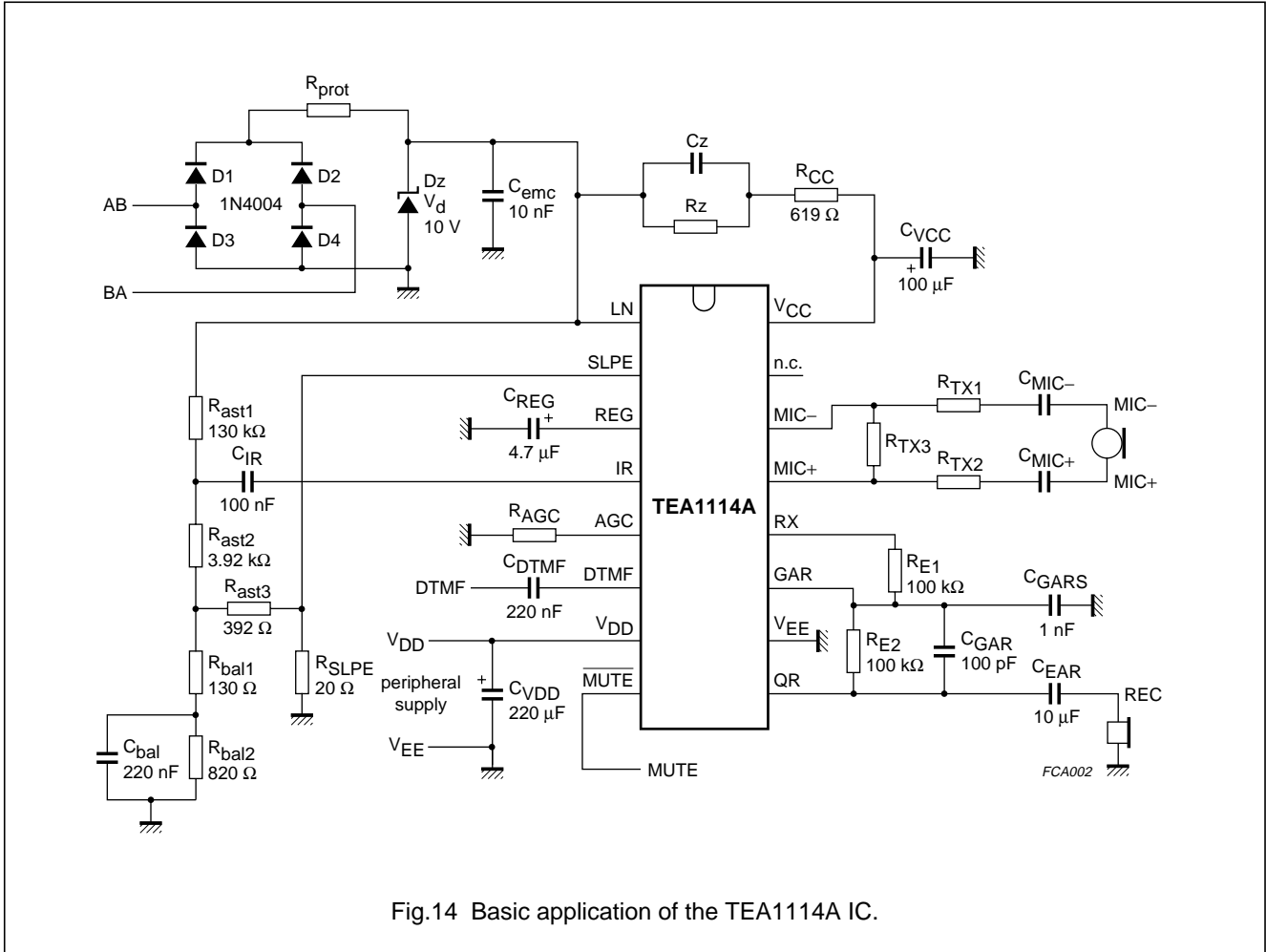
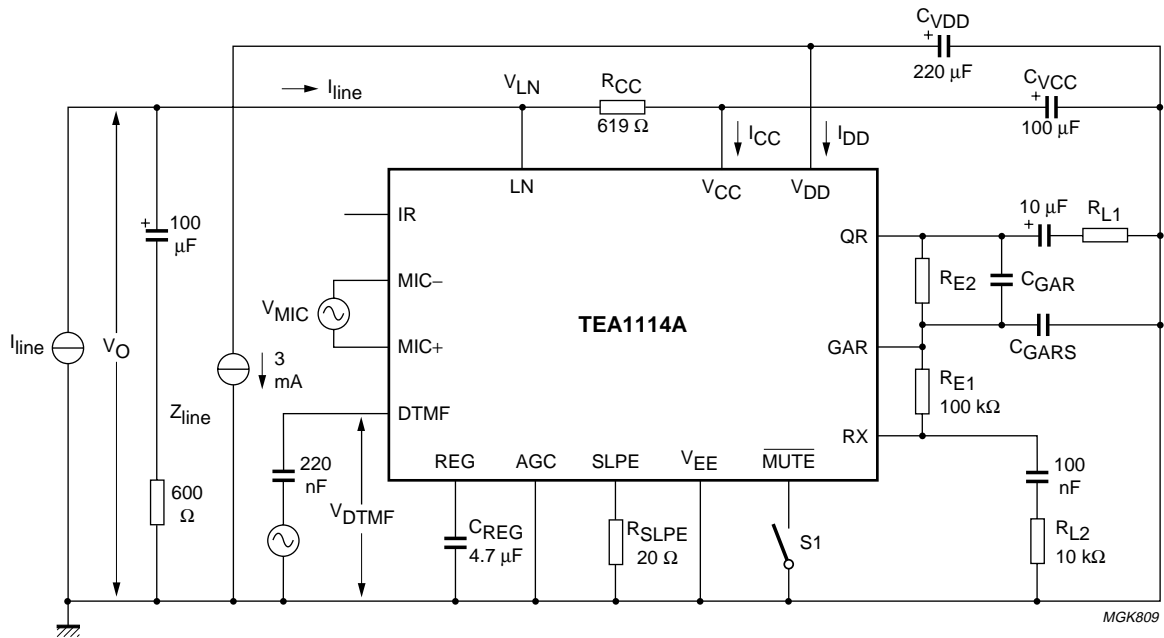


Fig.14 Basic application of the TEA1114A IC.

# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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Voltage gain defined as  $G_v = 20 \log \left| \frac{V_o}{V_i} \right|$ ;  $V_i = V_{MIC}$  or  $V_{DTMF}$ .

Microphone gain: S1 = open.

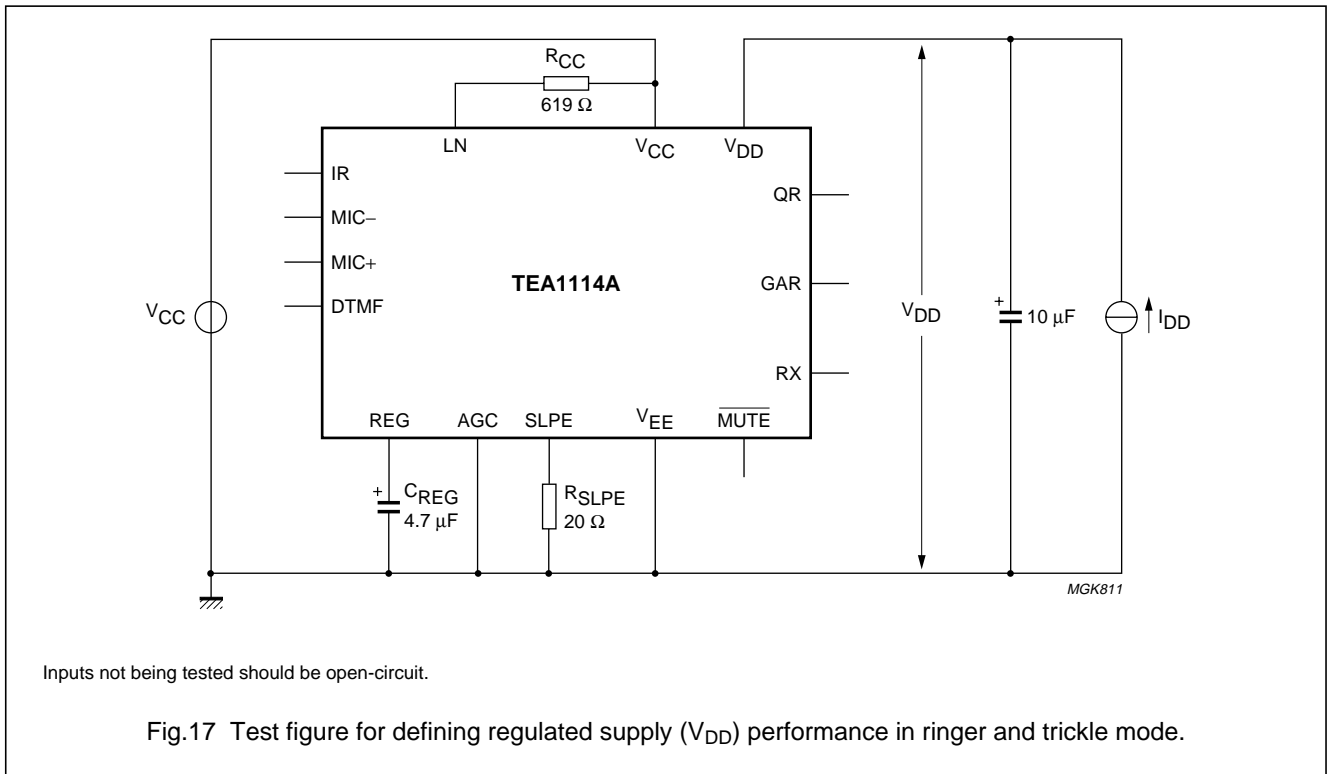
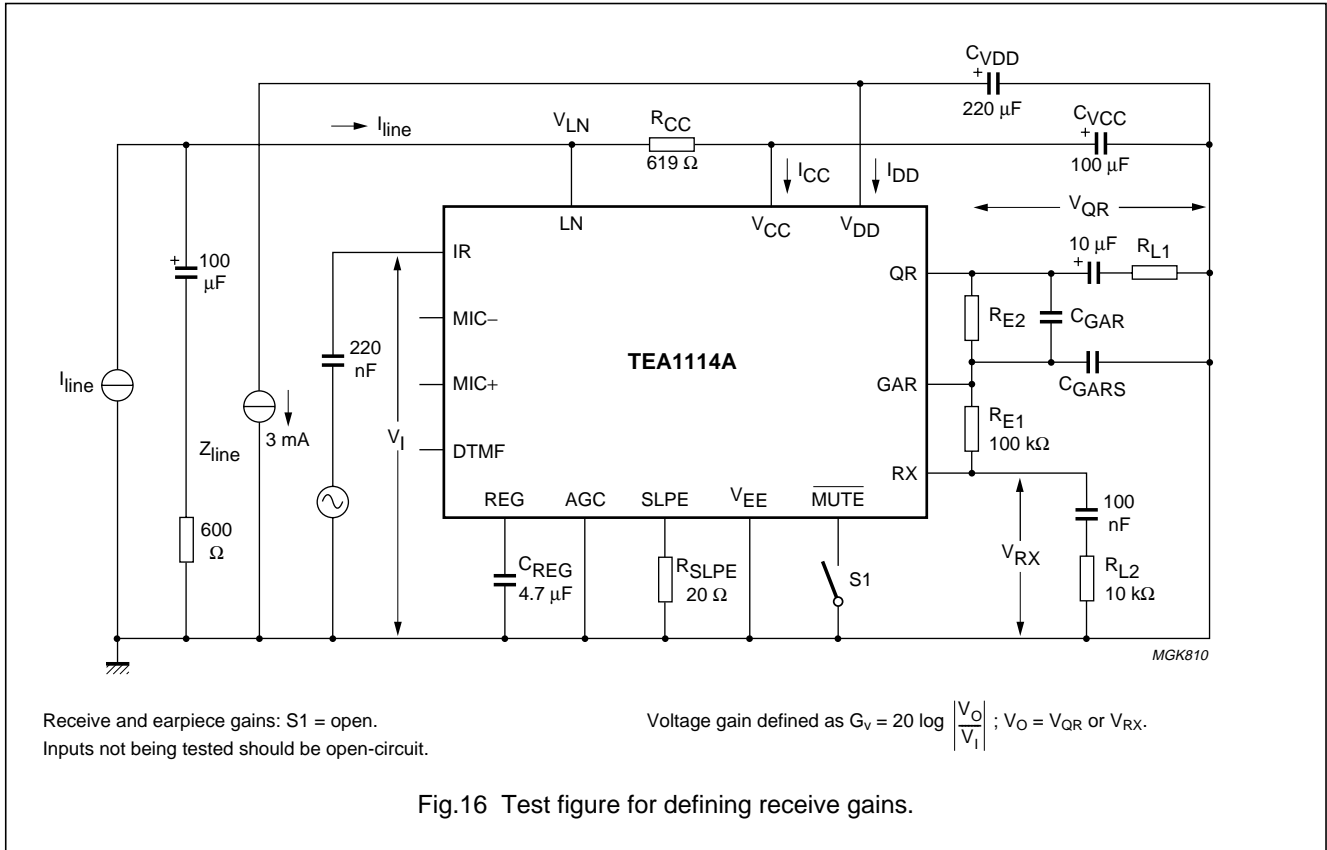
DTMF gain and confidence tone: S1 = closed.

Inputs not being tested should be open-circuit.

Fig.15 Test figure for defining transmit gains.

Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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**BONDING PAD LOCATIONS FOR TEA1114AUH**

All x/y coordinates represent the position of the centre of the pad (in  $\mu\text{m}$ ) with respect to the origin ( $x/y = 0/0$ ) of the die (see Fig.18). The size of all pads is  $80 \mu\text{m} \times 80 \mu\text{m}$ .

SYMBOL	PAD	COORDINATES	
		x	y
LN	1	99	365.7
SLPE	2	126	99
REG	3	377	99
IR	4	639	99
AGC	5	869	99
DTMF	6	1162	99
V <sub>DD</sub>	7	1343	104
MUTE	8	1366	333
QR	9	1366	531
n.c.	10	1366	1010
V <sub>EE</sub>	11	1370	1160
n.c.	12	1219.5	1160
GAR	13	1045	1160
RX	14	782.5	1160
MIC+	15	357.5	1160
MIC-	16	141.5	1160
V <sub>CC</sub>	17	99	963.5
n.c.	18	99	764
LN	19	99	570

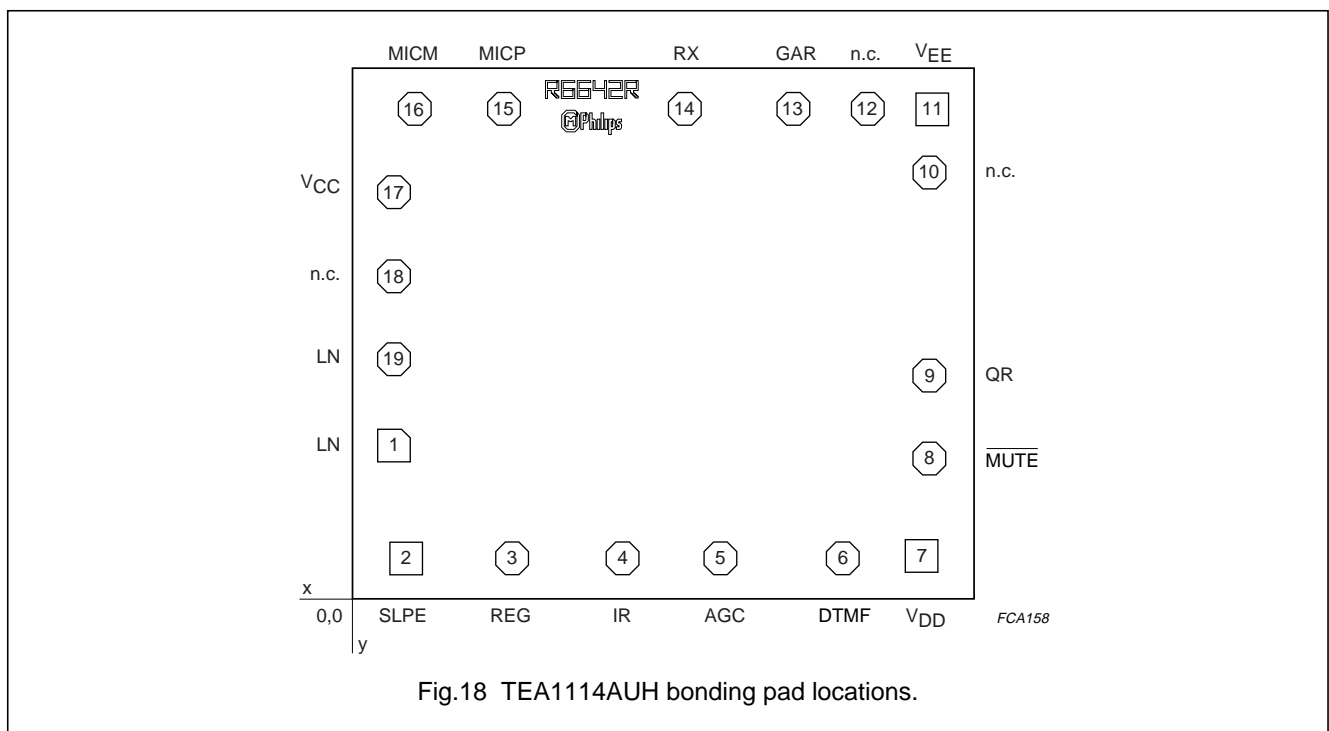


Fig.18 TEA1114AUH bonding pad locations.

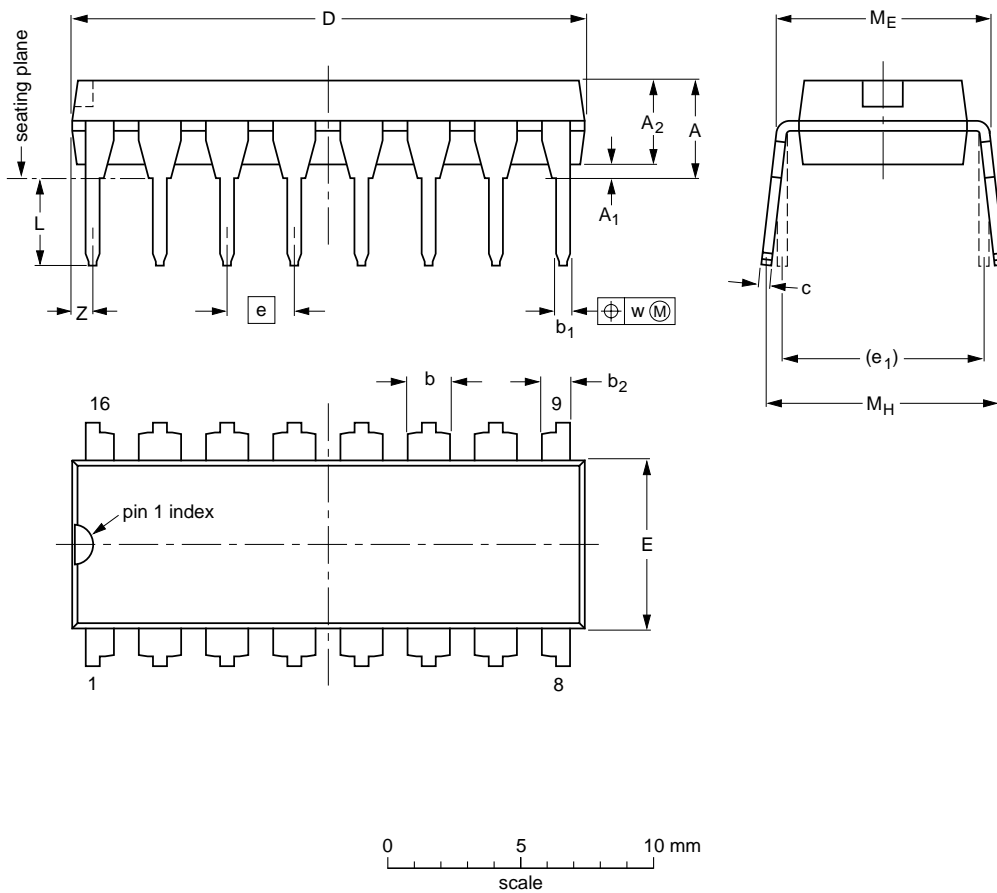
Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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PACKAGE OUTLINES

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	b <sub>2</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	e <sub>1</sub>	L	M <sub>E</sub>	M <sub>H</sub>	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.030

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

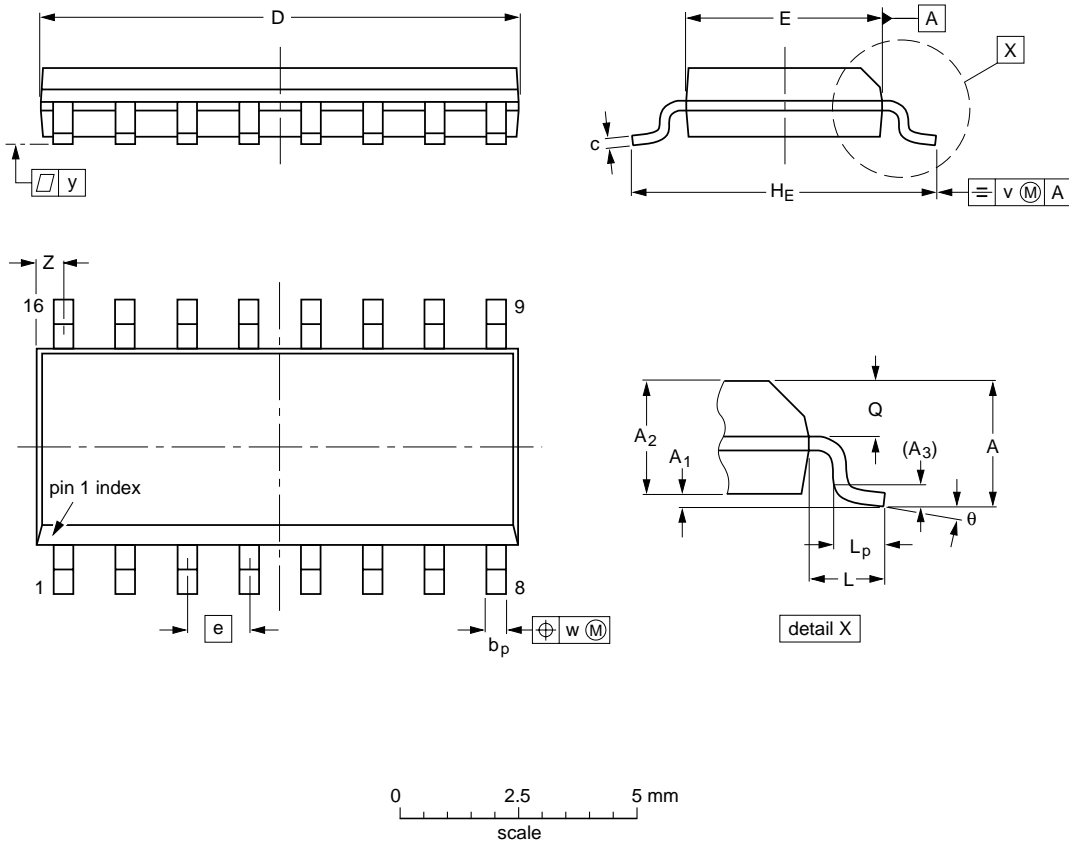
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT38-4						92-11-17 95-01-14

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SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT109-1	076E07	MS-012			97-05-22- 99-12-27

## Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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### SOLDERING

#### Introduction

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (document order number 9398 652 90011).

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mount components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

#### Through-hole mount packages

##### SOLDERING BY DIPPING OR BY SOLDER WAVE

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joints for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ( $T_{stg(max)}$ ). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

##### MANUAL SOLDERING

Apply the soldering iron (24 V or less) to the lead(s) of the package, either below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

#### Surface mount packages

##### REFLOW SOLDERING

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferably be kept below 230 °C.

##### WAVE SOLDERING

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

##### MANUAL SOLDERING

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.



# Low voltage telephone transmission circuit with dialler interface and regulated strong supply

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## Suitability of IC packages for wave, reflow and dipping soldering methods

MOUNTING	PACKAGE	SOLDERING METHOD		
		WAVE	REFLOW <sup>(1)</sup>	DIPPING
Through-hole mount	DBS, DIP, HDIP, SDIP, SIL	suitable <sup>(2)</sup>	–	suitable
Surface mount	BGA, SQFP	not suitable	suitable	–
	HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, SMS	not suitable <sup>(3)</sup>	suitable	–
	PLCC <sup>(4)</sup> , SO, SOJ	suitable	suitable	–
	LQFP, QFP, TQFP	not recommended <sup>(4)(5)</sup>	suitable	–
	SSOP, TSSOP, VSO	not recommended <sup>(6)</sup>	suitable	–

### Notes

- All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.
- For SDIP packages, the longitudinal axis must be parallel to the transport direction of the printed-circuit board.
- These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- Wave soldering is only suitable for LQFP, QFP and TQFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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## DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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**NOTES**

# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 3 Figtree Drive, HOMEBUSH, NSW 2140,  
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

**Belgium:** see The Netherlands

**Brazil:** see South America

**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor,  
51 James Bourchier Blvd., 1407 SOFIA,  
Tel. +359 2 68 9211, Fax. +359 2 68 9102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS,  
Tel. +1 800 234 7381, Fax. +1 800 943 0087

**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,  
Tel. +852 2319 7888, Fax. +852 2319 7700

**Colombia:** see South America

**Czech Republic:** see Austria

**Denmark:** Sydhavnsgade 23, 1780 COPENHAGEN V,  
Tel. +45 33 29 3333, Fax. +45 33 29 3905

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615 800, Fax. +358 9 6158 0920

**France:** 51 Rue Carnot, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Band Box Building, 2nd floor,  
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,  
Tel. +91 22 493 8541, Fax. +91 22 493 0966

**Indonesia:** PT Philips Development Corporation, Semiconductors Division,  
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,  
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,  
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),  
Tel. +39 039 203 6838, Fax +39 039 203 6800

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,  
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,  
Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,  
Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Pakistan:** see Singapore

**Philippines:** Philips Semiconductors Philippines Inc.,  
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,  
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Al.Jerozolimskie 195 B, 02-222 WARSAW,  
Tel. +48 22 5710 000, Fax. +48 22 5710 001

**Portugal:** see Spain

**Romania:** see Italy

**Russia:** Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,  
Tel. +7 095 755 6918, Fax. +7 095 755 6919

**Singapore:** Lorong 1, Toa Payoh, SINGAPORE 319762,  
Tel. +65 350 2538, Fax. +65 251 6500

**Slovakia:** see Austria

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**South Africa:** S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,  
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,  
Tel. +27 11 471 5401, Fax. +27 11 471 5398

**South America:** Al. Vicente Pinzon, 173, 6th floor,  
04547-130 SÃO PAULO, SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 821 2382

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 93 301 6312, Fax. +34 93 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,  
Tel. +41 1 488 2741 Fax. +41 1 488 3263

**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,  
TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

**Thailand:** PHILIPS ELECTRONICS (THAILAND) Ltd.,  
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,  
Tel. +66 2 745 4090, Fax. +66 2 398 0793

**Turkey:** Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,  
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
Tel. +1 800 234 7381, Fax. +1 800 943 0087

**Uruguay:** see South America

**Vietnam:** see Singapore

**Yugoslavia:** PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,  
Tel. +381 11 3341 299, Fax.+381 11 3342 553

**For all other countries apply to:** Philips Semiconductors,  
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